

Neil J Curson

List of Publications by Year in descending order

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41
papers

869
citations

471061

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476904

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docs citations

41
times ranked

910
citing authors

#	ARTICLE	IF	CITATIONS
1	Microwave Properties of 2D CMOS Compatible Co-planar Waveguides Made from Phosphorus Dopant Monolayers in Silicon. <i>Advanced Electronic Materials</i> , 2022, 8, .	2.6	0
2	In operando charge transport imaging of atomically thin dopant nanostructures in silicon. <i>Nanoscale</i> , 2022, , .	2.8	1
3	Modification of the Ge(001) Subsurface Electronic Structure after Adsorption of Sn. <i>Applied Surface Science</i> , 2022, , 153884.	3.1	0
4	The formation of a Sn monolayer on Ge(1 0 0) studied at the atomic scale. <i>Applied Surface Science</i> , 2021, 561, 149961.	3.1	3
5	Substitutional Tin Acceptor States in Black Phosphorus. <i>Journal of Physical Chemistry C</i> , 2021, 125, 22883-22889.	1.5	5
6	Nanoscale imaging of mobile carriers and trapped charges in delta doped silicon p-n junctions. <i>Nature Electronics</i> , 2020, 3, 531-538.	13.1	24
7	Atomic-Scale Patterning of Arsenic in Silicon by Scanning Tunneling Microscopy. <i>ACS Nano</i> , 2020, 14, 3316-3327.	7.3	36
8	Topological phases of a dimerized Fermi-Hubbard model for semiconductor nano-lattices. <i>Npj Quantum Information</i> , 2020, 6, .	2.8	27
9	Two- to three-dimensional crossover in a dense electron liquid in silicon. <i>Physical Review B</i> , 2018, 97, .	1.1	5
10	Higher order reconstructions of the Ge(001) surface induced by a Ba layer. <i>Applied Surface Science</i> , 2018, 435, 438-443.	3.1	2
11	Local anodic oxidation lithography on organic semiconductor crystals: Oxide depth revealed by conductance tomography. <i>Organic Electronics</i> , 2018, 63, 231-236.	1.4	4
12	Exact location of dopants below the Si(001):H surface from scanning tunneling microscopy and density functional theory. <i>Physical Review B</i> , 2017, 95, .	1.1	10
13	Nondestructive imaging of atomically thin nanostructures buried in silicon. <i>Science Advances</i> , 2017, 3, e1602586.	4.7	56
14	Channels of oxygen diffusion in single crystal rubrene revealed. <i>Physical Chemistry Chemical Physics</i> , 2016, 18, 32302-32307.	1.3	2
15	Imaging of buried phosphorus nanostructures in silicon using scanning tunneling microscopy. <i>Applied Physics Letters</i> , 2014, 104, .	1.5	8
16	Investigating individual arsenic dopant atoms in silicon using low-temperature scanning tunnelling microscopy. <i>Journal of Physics Condensed Matter</i> , 2014, 26, 012001.	0.7	28
17	Revealing surface oxidation on the organic semi-conducting single crystal rubrene with time of flight secondary ion mass spectroscopy. <i>Physical Chemistry Chemical Physics</i> , 2013, 15, 5202.	1.3	6
18	Studying atomic scale structural and electronic properties of ion implanted silicon samples using cross-sectional scanning tunneling microscopy. <i>Applied Physics Letters</i> , 2013, 102, 012107.	1.5	8

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19	Site-Dependent Ambipolar Charge States Induced by Group V Atoms in a Silicon Surface. ACS Nano, 2012, 6, 10456-10462.	7.3	14
20	Model system for controlling strain in silicon at the atomic scale. Physical Review B, 2011, 84, .	1.1	6
21	Single Phosphorus Atoms in Si(001):â€‰ Doping-Induced Charge Transfer into Isolated Si Dangling Bonds. Journal of Physical Chemistry C, 2007, 111, 6428-6433.	1.5	5
22	Doping and STM tip-induced changes to single dangling bonds on Si(001). Surface Science, 2007, 601, 4036-4040.	0.8	10
23	Phosphine Dissociation and Diffusion on Si(001) Observed at the Atomic Scale. Journal of Physical Chemistry B, 2006, 110, 3173-3179.	1.2	28
24	Phosphorus and hydrogen atoms on the (001) surface of silicon: A comparative scanning tunnelling microscopy study of surface species with a single dangling bond. Surface Science, 2006, 600, 318-324.	0.8	20
25	Towards the Routine Fabrication of P in Si Nanostructures: Understanding P Precursor Molecules on Si(001). Materials Research Society Symposia Proceedings, 2005, 864, 541.	0.1	2
26	Observation of substitutional and interstitial phosphorus on cleanSi(100)â€ˆ(2Å–1)with scanning tunneling microscopy. Physical Review B, 2005, 72, .	1.1	11
27	Effective removal of hydrogen resists used to pattern devices in silicon using scanning tunneling microscopy. Applied Physics Letters, 2005, 86, 143116.	1.5	11
28	Scanning probe microscopy for silicon device fabrication. Molecular Simulation, 2005, 31, 505-515.	0.9	50
29	Measurement of phosphorus segregation in silicon at the atomic scale using scanning tunneling microscopy. Applied Physics Letters, 2004, 85, 1359-1361.	1.5	49
30	Toward Atomic-Scale Device Fabrication in Silicon Using Scanning Probe Microscopy. Nano Letters, 2004, 4, 1969-1973.	4.5	150
31	Towards the atomic-scale fabrication of a silicon-based solid state quantum computer. Surface Science, 2003, 532-535, 1209-1218.	0.8	23
32	STM investigation of epitaxial Si growth for the fabrication of a Si-based quantum computer. Applied Surface Science, 2003, 212-213, 319-324.	3.1	16
33	Challenges in Surface Science for a P-in-Si Quantum Computer â€ˆ Phosphine Adsorption/Incorporation and Epitaxial Si Encapsulation. Surface Review and Letters, 2003, 10, 415-423.	0.5	2
34	Encapsulation of phosphorus dopants in silicon for the fabrication of a quantum computer. Applied Physics Letters, 2002, 81, 3197-3199.	1.5	92
35	Scanning tunnelling microscope fabrication of arrays of phosphorus atom qubits for a silicon quantum computer. Smart Materials and Structures, 2002, 11, 741-748.	1.8	8
36	Imaging charged defects on clean Si(100)-(2Å–1) with scanning tunneling microscopy. Journal of Applied Physics, 2002, 92, 820-824.	1.1	35

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37	An AFM study of the processing of hydrogen passivated silicon(111) of a low miscut angle. Surface Science, 2001, 490, 285-295.	0.8	22
38	Ballistic transport in a GaAs/Al _x Ga _{1-x} As one-dimensional channel fabricated using an atomic force microscope. Applied Physics Letters, 2001, 78, 3466-3468.	1.5	21
39	Single Photon Detection with a Quantum Dot Transistor. Japanese Journal of Applied Physics, 2001, 40, 2058-2064.	0.8	43
40	Construction of a silicon-based solid state quantum computer. Quantum Information and Computation, 2001, 1, 82-95.	0.1	7
41	Interaction of silane with Cu(111): Surface alloy and molecular chemisorbed phases. Physical Review B, 1997, 55, 10819-10829.	1.1	19